

	Type	L #	Hits	Search Text	DBs
1	BRS	L1	2	"6744482".pn.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
2	BRS	L2	0	(oixel near electrode\$1) near25 (electroluminescence or el)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
3	BRS	L3	1202	(pixel near electrode\$1) near25 (electroluminescence or el)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
4	BRS	L4	0	(pixel near electrode\$1) near25 (electroluminescence)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
5	BRS	L5	0	(pixel near electrode\$1) near25 (electro- luminescence)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
6	BRS	L6	1202	(pixel near electrode\$1) near25 (el)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
7	BRS	L7	518	((pixel near electrode\$1) near25 (el)) near25 (hole\$1 or aperture\$1 or recess\$2 or via\$1 or open\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
8	BRS	L8	1	((((pixel near electrode\$1) near25 (el)) near25 (hole\$1 or aperture\$1 or recess\$2 or via\$1 or open\$3)) near25 (silicon near nitride or sin)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
9	BRS	L9	383	((pixel near electrode\$1) near25 (el)) near25 (hole\$1 or aperture\$1 or recess\$2 or via\$1 or open\$3)) and (silicon near nitride)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
10	BRS	L10	1	((pixel near electrode\$1) near25 (el)) near25 (hole\$1 or aperture\$1 or recess\$2 or via\$1 or open\$3)) same (silicon near nitride)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
11	BRS	L11	401	((pixel near electrode\$1) near25 (el)) near25 (hole\$1 or aperture\$1 or recess\$2 or via\$1 or open\$3)) and (silicon near nitride or sin)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
12	BRS	L12	2	((((pixel near electrode\$1) near25 (el)) near25 (hole\$1 or aperture\$1 or recess\$2 or via\$1 or open\$3)) and (silicon near nitride or sin)) near35 (substrate)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
13	BRS	L13	0	(((((pixel near electrode\$1) near25 (el)) near25 (hole\$1 or aperture\$1 or recess\$2 or via\$1 or open\$3)) and (silicon near nitride or sin)) near35 (wafer)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
14	BRS	L14	0	("2004/0207331").URPN.	USPAT